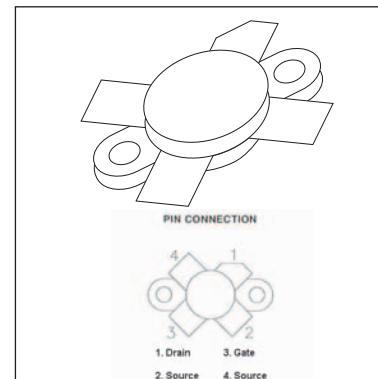


## RF POWER VERTICAL MOSFET

The VRF150 is a gold metallized silicon, n-channel RF power transistor designed for broadband commercial and military applications requiring high power and gain without compromising reliability, ruggedness, and inter-modulation distortion.



### FEATURES

- 150W with 11dB Typical Gain @ 150MHz, 50V
- 150W with 18dB Min. Gain @ 30MHz, 50V
- Excellent Stability & Low IMD
- Common Source Configuration
- 30:1 Load VSWR Capability at Specified Operating Conditions
- Nitride Passivated
- Refractory Gold Metallization

### Maximum Ratings

All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified

Symbol	Parameter	VRF150	Unit
$V_{DD}$	Drain-Source Voltage	160	Volts
$V_{DGO}$	Drain-Gate Voltage	160	
$I_D$	Continuous Drain Current @ $T_C = 25^\circ\text{C}$	16	Amps
$V_{GS}$	Gate-Source Voltage	$\pm 40$	Volts
$P_D$	Total Device Dissipation @ $T_C = 25^\circ\text{C}$	300	Watts
$T_{STG}$	Storage Temperature Range	-65 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature	200	

### Static Electrical Characteristics

Symbol	Parameter	Min	Typ	Max	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage ( $V_{GS} = 0V, I_D = 100\text{mA}$ )	160	180		Volts
$V_{DS(ON)}$	On State Drain Voltage ( $I_{D(ON)} = 10A, V_{GS} = 10V$ )	1.0	2.0	5.0	
$I_{DSS}$	Zero Gate Voltage Drain Current ( $V_{DS} = 50V, V_{GS} = 0V$ )			5.0	mA
$I_{GSS}$	Gate-Source Leakage Current ( $V_{GS} = \pm 20V, V_{DS} = 0V$ )			1.0	$\mu\text{A}$
$g_{fs}$	Forward Transconductance ( $V_{DS} = 10V, I_D = 5A$ )	4.5			mhos
$V_{GS(TH)}$	Gate Threshold Voltage ( $V_{DS} = 10V, I_D = 100\text{mA}$ )	2		5	Volts

### Thermal Characteristics

Symbol	Characteristic	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction to Case Thermal Resistance			0.60	$^\circ\text{C/W}$

## DYNAMIC CHARACTERISTICS

VRF150

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$C_{iss}$	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 50V$ $f = 1MHz$		480		pF
$C_{oss}$	Output Capacitance			230		
$C_{rss}$	Reverse Transfer Capacitance			40		

## FUNCTIONAL CHARACTERISTICS

Symbol	Test Conditions	Min	Typ	Max	Unit
$G_{PS}$	$f = 30MHz, V_{DD} = 50V, I_{DQ} = 250mA, P_{out} = 150W_{PEP}$	18			dB
$G_{PS}$	$f = 150MHz, V_{DD} = 50V, I_{DQ} = 250mA, P_{out} = 150W_{PEP}$		11		
$\eta_D$	$f = 150MHz, V_{DD} = 50V, I_{DQ} = 250mA, P_{out} = 150W_{PEP}$		50		%
$IMD_{(d3)}$	$f1 = 30MHz, f2 = 30.001MHz, V_{DD} = 50V, I_{DQ} = 250mA, P_{out} = 150W_{PEP}$ ①		-32		dBc
$IMD_{(d11)}$	$f1 = 30MHz, f2 = 30.001MHz, V_{DD} = 50V, I_{DQ} = 250mA, P_{out} = 150W_{PEP}$		-60		
$\psi$	$f = 30MHz, V_{DD} = 50V, I_{DQ} = 250mA, P_{out} = 150W_{PEP}$ 30:1VSWR - All Phase Angles	No Degradation in Output Power			

## Class A Characteristics

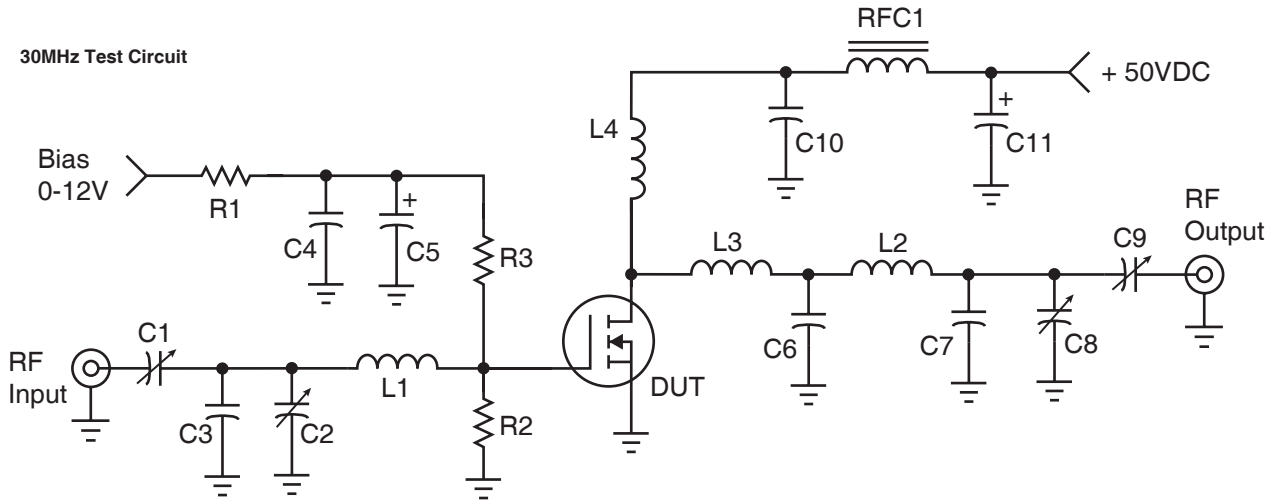
Symbol	Test Conditions	Min	Typ	Max	Unit
$G_{PS}$	$V_{DD} = 50V, I_{DQ} = 3A, P_{out} = 50W_{PEP}, f1 = 30MHz, f2 = 30.001MHz$		20		dB
$IMD_{(d3)}$			-50		
$IMD_{(d9-d13)}$			-75		

### NOTE:

① To MIL-STD-1311 Version A, test method 2204B, Two Tone, Reference Each Tone

Microsemi reserves the right to change, without notice, the specifications and information contained herein.

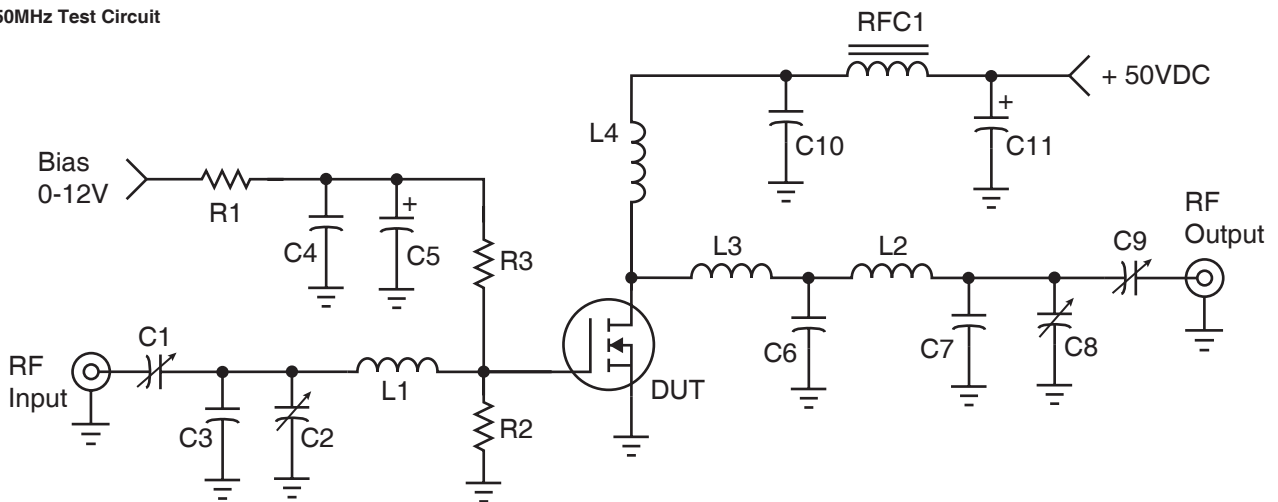
30MHz Test Circuit



- C1, C2, C8 -- Arco 463 or equivalent
- C3 -- 25pF, Unelco
- C4 -- 0.1uF, Ceramic
- C5 -- 1.0uF, 15 WV Tantalum
- C6 -- 250pF, Unelco J101
- C7-- 25pF, Unelco J101
- C9 -- Arco 262 or equivalent
- C10 -- 0.05uF, Ceramic
- C11 -- 15uF, 60WV Electrolytic

- L1 -- 3/4", #18 into Hairpin
- L2 -- Printed Line, 0.200" W x 0.500" L
- L3 -- 1", #16 into Hairpin approx 16nH
- L4 -- 2 turns #16, 5/16" ID
- RFC1 - VK200-4B
- R1 -- 150Ω, 1/2W Carbon
- R2 -- 10kΩ, 1/2W Carbon
- R3 -- 120Ω, 1/2W Carbon

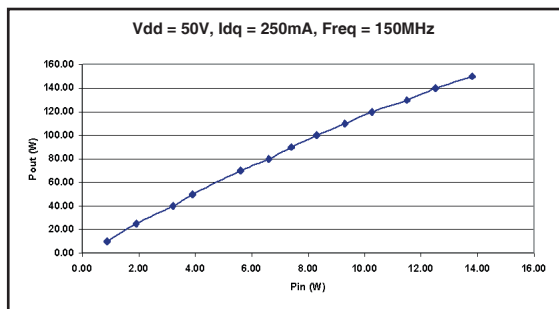
150MHz Test Circuit



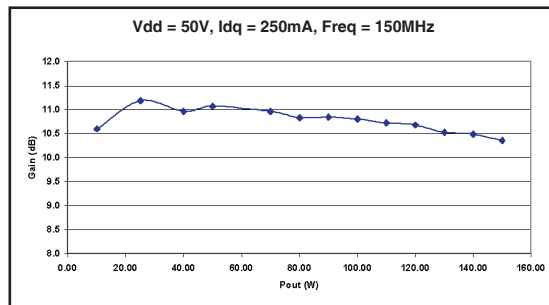
- C1, C2, C8 -- Arco 463 or equivalent
- C3 -- 25pF, Unelco
- C4 -- 0.1uF, Ceramic
- C5 -- 1.0uF, 15 WV Tantalum
- C6 -- 250pF, Unelco J101
- C7-- 25pF, Unelco J101
- C9 -- Arco 262 or equivalent
- C10 -- 0.05uF, Ceramic
- C11 -- 15uF, 60WV Electrolytic

- L1 -- 3/4", #18 into Hairpin
- L2 -- Printed Line, 0.200" W x 0.500" L
- L3 -- 1", #16 into Hairpin approx 16nH
- L4 -- 2 turns #16, 5/16" ID
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- R3 -- 120Ω, 1/2W Carbon

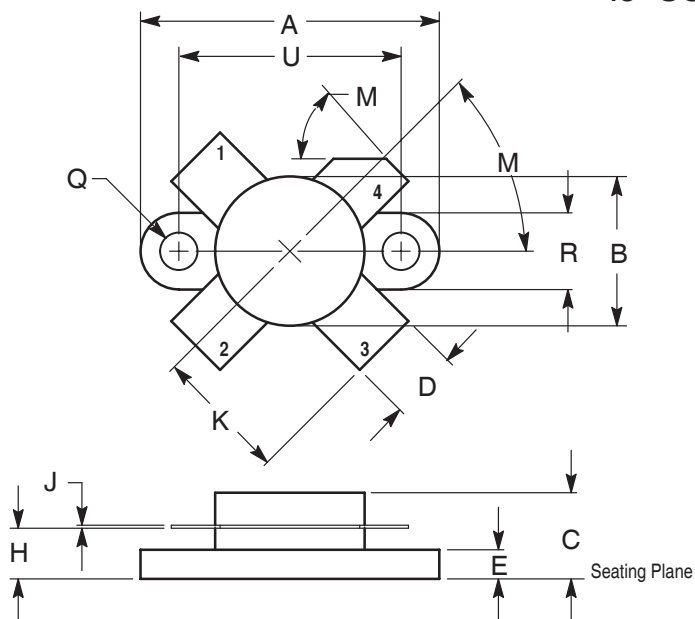
Power Out vs. Power In



Gain vs. Power Out



.5" SOE Package Outline



- PIN 1. SOURCE
- 2. GATE
- 3. SOURCE
- 4. DRAIN

2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.960	0.990	24.39	25.14
B	0.465	0.510	11.82	12.95
C	0.229	0.275	5.82	6.98
D	0.216	0.235	5.49	5.96
E	0.084	0.110	2.14	2.79
H	0.144	0.178	3.66	4.52
J	0.003	0.007	0.08	0.17
K	0.435		11.0	
M	45° NOM		45° NOM	
Q	0.115	0.130	2.93	3.30
R	0.246	0.255	6.25	6.47
U	0.720	0.730	18.29	18.54